COMPLIANT

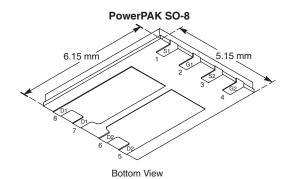
HALOGEN

FREE



Dual N-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$ I_{D}			
150	0.150 at V _{GS} = 10 V	3.3		
	0.168 at V _{GS} = 6 V	3.1		



Ordering Information: Si7946DP-T1-E3 (Lead (Pb)-free)

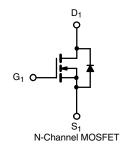
Si7946DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

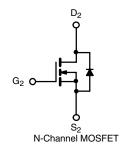
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFETs
- New Low Thermal Resistance PowerPAK[®] Package
- Dual MOSFET for Space Savings
- · PWM Optimized for Fast Switching
- Avalanche Rated

APPLICATIONS

Primary Side Switch





ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise n	oted		
Parameter		Symbol	10 s Steady State		Unit
Drain-Source Voltage		V_{DS}	150		V
Gate-Source Voltage		V _{GS}	± 20		V
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	I _D	3.3	2.1	
Continuous Drain Current (1) = 150 °C)	T _A = 70 °C		2.6	1.7	
Pulsed Drain Current		I _{DM}	10		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.2	
Single Avalanche Current	L = 0.1 mH	I _{AS}	9		
Single Avalanche Energy		E _{AS}	4		mJ
Marian and David Discipation a	T _A = 25 °C	P _D	3.5	1.4	W
Maximum Power Dissipation ^a	T _A = 70 °C		2.2	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manine Investiga to Ambienta	t ≤ 10 s	- R _{thJA}	26	35	°C/W
Maximum Junction-to-Ambient ^a	Steady State		60	85	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	3.2	4.2	1

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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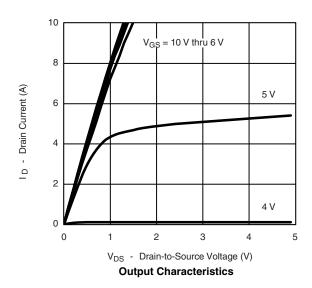
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Condition	Test Condition Min.		Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	1	V _{DS} = 150 V, V _{GS} = 0 V			1	μΑ	
Zero Gate voltage Drain Current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V, T _J = 55 °C			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
5	В	$V_{GS} = 10 \text{ V}, I_D = 3.3 \text{ A}$		0.124	0.150	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6 \text{ V}, I_D = 3.1 \text{ A}$		0.137	0.168	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 3.3 \text{ A}$		9		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.87	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			12.6	20	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3.3 \text{ A}$		2.8			
Gate-Drain Charge	Q_{gd}			4.5			
Gate Resistance	R_g	f = 1 MHz		3.5		Ω	
Turn-On Delay Time	t _{d(on)}			11	20		
Rise Time	t _r	$ \begin{array}{c c} t_r & V_{DD} = 75 \text{ V, } R_L = 75 \Omega \\ \hline t_{d(off)} & I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 6 \Omega \\ \end{array} $		15	25	ns	
Turn-Off Delay Time	t _{d(off)}			30	45		
Fall Time	t _f			20	30		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.9 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		62	100		

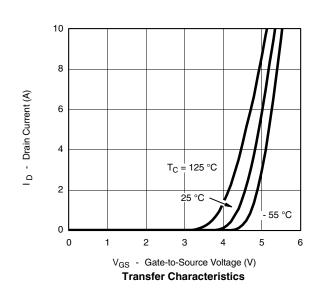
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



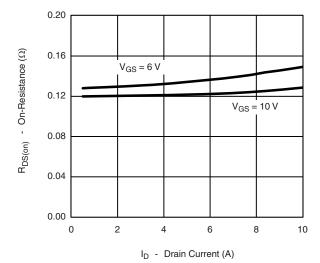




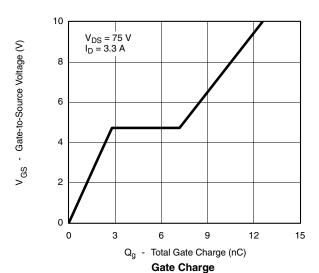


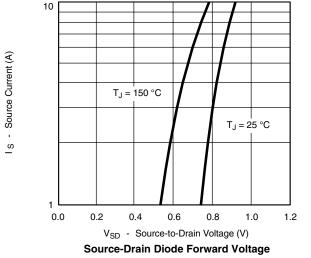


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

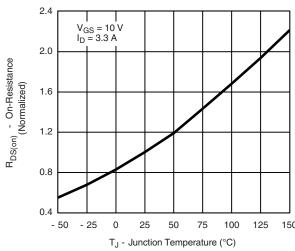


On-Resistance vs. Drain Current

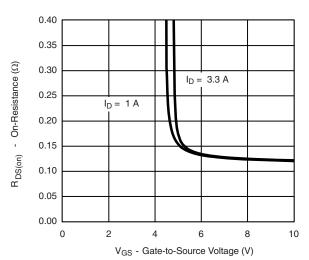




1000 800 C - Capacitance (pF) Ciss 600 400 200 $\mathsf{C}_{\mathsf{rss}}$ 0 10 20 30 40 50 60 70 80



On-Resistance vs. Junction Temperature

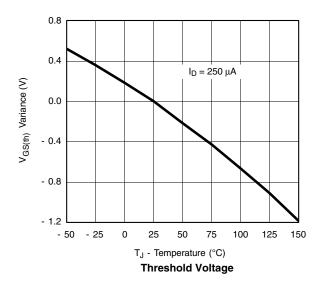


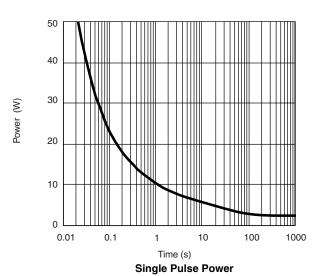
On-Resistance vs. Gate-to-Source Voltage

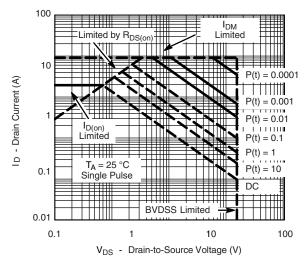
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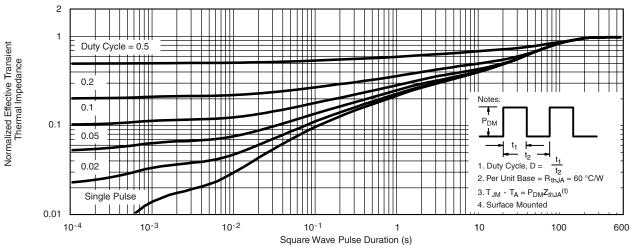
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





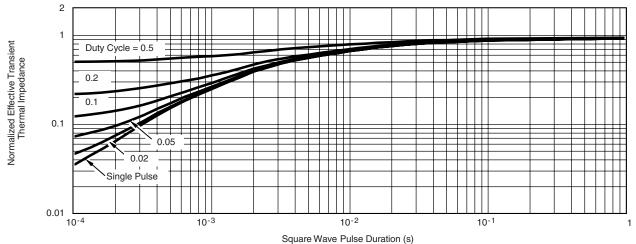


Safe Operating Area, Junction-to-Ambient





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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